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United States Patent [19]

Fazio

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[54] FLASH MEMORY DEVICE HAVING A PAGE
MODE OF OPERATION

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[63] Continuation of Ser. No. 699,490, Aug. 19, 1996, abandoned.

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365/185.12; 365/185.13; 365/185.03[58] Field of Search 365/185.21, 185.26,
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[57] ABSTRACT

A method for determining data stored by a memory cell. The memory cell has a select gate coupled to a wordline, a first electrode coupled to a bitline, and a second electrode coupled to a conductor. The method comprises: floating the bitline; applying a first voltage to the wordline; applying a second voltage to the conductor such that the bitline is set to a third voltage that is equal to the first voltage minus a threshold voltage of the memory cell; and sensing the third voltage to determine the data stored by the memory cell.

18 Claims, 8 Drawing Sheets

